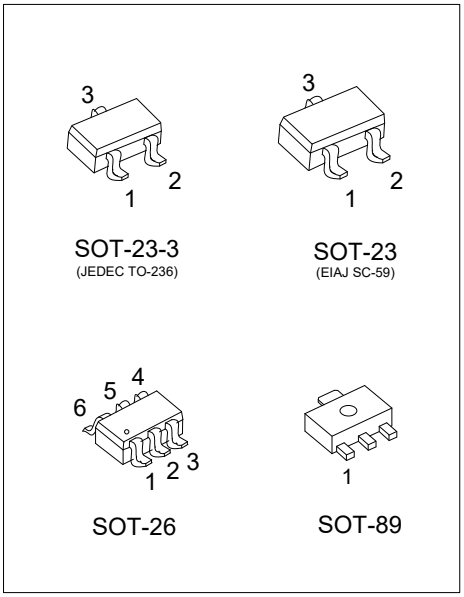
2SC3356

NPN SILICON TRANSISTOR

HIGH FREQUENCY LOW NOISE AMPLIFIER



■ DESCRIPTION

The UTC **2SC3356** is an NPN silicon epitaxial transistor designed for low noise amplifier at VHF, UHF and CATV band.

It has large dynamic range and good current characteristic..

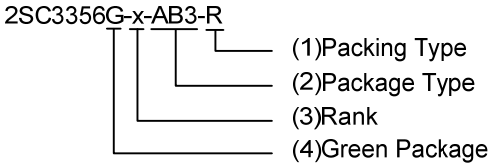
■ FEATURES

* Low Noise and High Gain
* High Power Gain

■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment						Packing
Lead Free	Halogen Free		1	2	3	4	5	6	
2SC3356L-x-AB3-R	2SC3356G-x-AB3-R	SOT-89	B	C	E	-	-	-	Tape Reel
2SC3356L-x-AE2-R	2SC3356G-x-AE2-R	SOT-23-3	B	E	C	-	-	-	Tape Reel
2SC3356L-x-AE3-R	2SC3356G-x-AE3-R	SOT-23	B	E	C	-	-	-	Tape Reel
2SC3356L-x-AG6-R	2SC3356G-x-AG6-R	SOT-26	C	C	B	E	C	C	Tape Reel

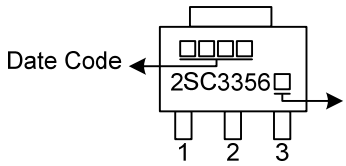
Note: Pin Assignment: B: Base E: Emitter C: Collector

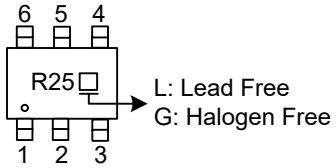


(1) R: Tape Reel
(2) AB3: SOT-89, AE2: SOT-23-3, AE3: SOT-23
AG6: SOT-26
(3) x: refer to Classification of h_{FE}
(4) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING

SOT-23-3/SOT-23	
2SC3356L	2SC3356G
R25	R25G
SOT-89	SOT-26





■ ABSOLUTE MAXIMUM RATING

PARAMETER		SYMBOL	RATINGS	UNIT
Collector to Base Voltage		BV_{CBO}	20	V
Collector to Emitter Voltage		BV_{CEO}	12	V
Emitter to Base Voltage		BV_{EBO}	3	V
Collector Current		I_C	100	mA
Power Dissipation	SOT-89	P_D	500	mW
	SOT-23-3 SOT-23 SOT-26		200	mW
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-65 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

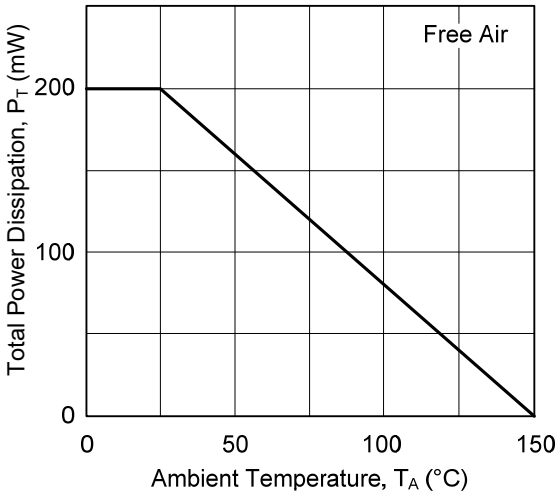
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector to Base Breakdown Voltage	BV_{CBO}	I_C=10μA, I_E=0	20			V
Collector to Emitter Breakdown Voltage	BV_{CEO}	I_C=1mA, R_{BE}=∞	12			V
Emitter to Base Breakdown Voltage	BV_{EBO}	I_E=10μA, I_C=0	3			V
Collector-Base Cut-Off Current	I_{CBO}	V_{CB} =10V,I_E =0			1.0	μA
Emitter-Base Cut-Off Current	I_{EBO}	V_{EB} =1 V, I_C=0			1.0	μA
DC Current Gain	h_{FE}	V_{CE} =10 V, I_C =20 mA	50		300	
Gain Bandwidth Product	f_T	V_{CE} =10 V, I_C =20 mA		7		GHz
Feed-Back Capacitance	C_{RE}	V_{CB} =10 V, I_E =0, f =1.0MHz			1.0	pF
Noise Figure	NF	V_{CE} =10 V, I_C =7mA, f =1.0GHz			2.0	dB

■ CLASSIFICATION OF h_{FE}

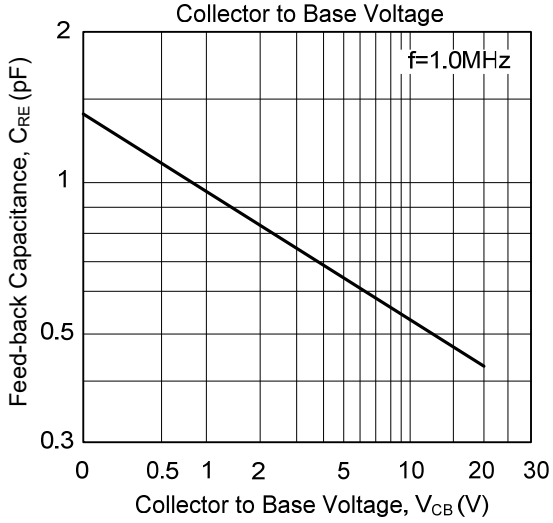
RANK	A	B
RANGE	50-170	160-300

■ TYPICAL CHARACTERISTICS

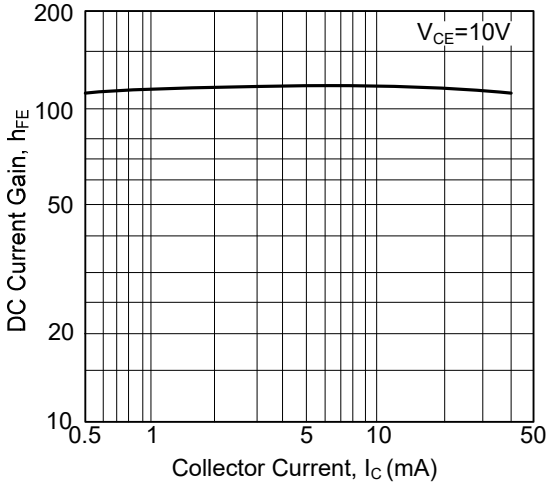
Total Power Dissipation vs. Ambient Temperature



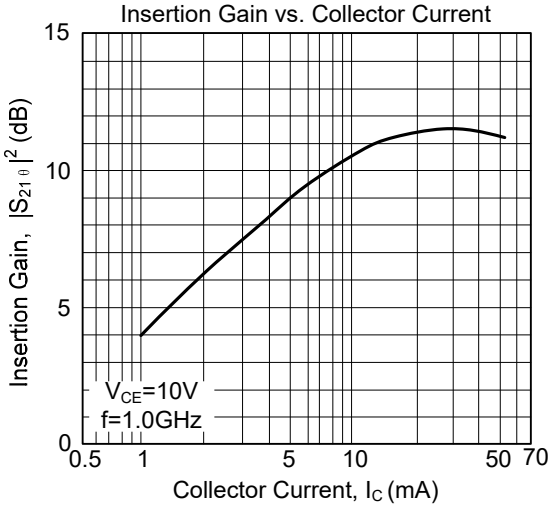
Feed-back Capacitance vs. Collector to Base Voltage



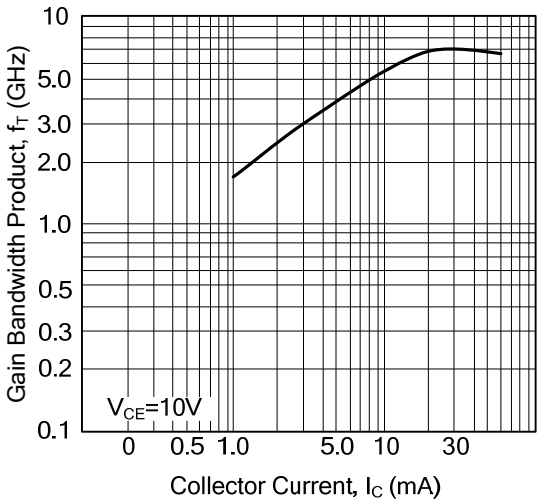
DC Current Gain vs. Collector Current



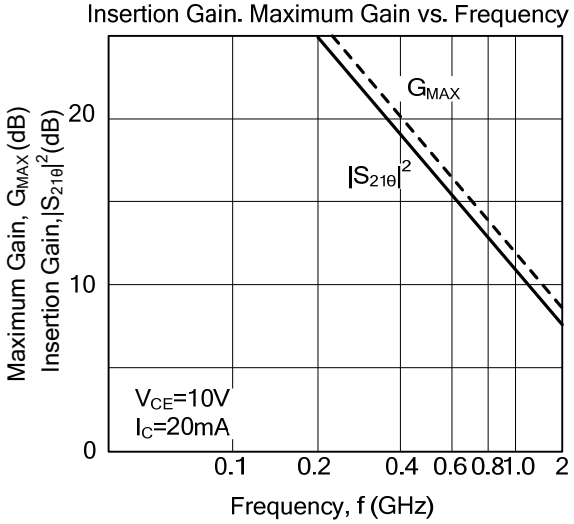
Insertion Gain vs. Collector Current



Gain Bandwidth Product vs. Collector Current



Insertion Gain. Maximum Gain vs. Frequency



■ TYPICAL CHARACTERISTICS (Cont.)